L Number	Hits	Search Text	DB	Time stamp
13	900	conduct\$6 and In near5 Ga near5 N	USPAT; US-PGPUB; EPO; JPO;	2004/04/21 16:25
14	75	(conduct\$6 with (In near5 Ga near5 N))	DERWENT USPAT; US-PGPUB; EPO; JPO;	2004/04/21 16:25
15	69	(conduct\$6 with (In near5 Ga near5 N))	DERWENT USPAT; EPO; JPO;	2004/04/21 16:26
16	3	((conduct\$7 near1 (layer or region or medium)) with (In near5 Ga near5 N))	DERWENT USPAT; EPO; JPO; DERWENT	2004/04/21 16:27
-	131	(nitride near semiconductor) and (buffer near layer) and (active near layer) and (clad\$5 near layer) and indium and substrate and electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/04/21 16:24
-	20	(nitride near semiconductor) and ((buffer near layer) with indium) and (active near layer) and (clad\$5 near layer) and substrate and electrode	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/01/06 11:28
-	28	(nitride near semiconductor) and (buffer near layer) and (active near layer) and (clad\$5 near layer) and indium and substrate and electrode and absorb\$6	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/19 14:52
-	21	((nitride near semiconductor) and (buffer near layer) and (active near layer) and (clad\$5 near layer) and indium and substrate and electrode and absorb\$6) not ((nitride near semiconductor) and ((buffer near layer) with indium) and (active near layer) and (clad\$5 near layer) and substrate and	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/19 14:52
-	6	electrode) (laser near chip) and (photoelectric or (photo adj electric)) and block\$6 and buffer and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/19 17:42
-	160	(laser near semiconductor) and (photoelectric or (photo adj electric)) and block\$6 and buffer and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/11 11:18
-	14	(laser near semiconductor) and (photoelectric or (photo adj electric)) and block\$6 and buffer and substrate and (laser near3 chip)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/19 17:46
-	171	(laser near semiconductor) and (photoelectric or (photo adj electric) or (photodetector) (photodiode) or (photo adj detector) or (photo ajd diode)) and block\$6 and buffer and substrate and (laser near3 chip)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/20 07:00
-	72	(semiconductor near laser near3 chip) and (photoelectric or (photo adj electric) or (photodetector) (photodiode) or (photo adj detector) or (photo ajd diode)) and block\$6 and buffer and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/20 07:03

L Number	Hits	Search Text	DB	Time stamp
13	900	conduct\$6 and In near5 Ga near5 N	USPAT;	2004/04/21 16:25
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
14	<i>7</i> 5	(conduct\$6 with (In near5 Ga near5 N))	USPAT;	2004/04/21 16:25
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
15	69	(conduct\$6 with (In near5 Ga near5 N))	USPAT;	2004/04/21 16:26
			EPO; JPO;	
	_		DERWENT	
16	3	((conduct\$7 near1 (layer or region or medium)) with (In near5	USPAT;	2004/04/21 16:52
		Ga near5 N))	EPO; JPO;	
		/ 1 .0m .1/1	DERWENT	
17	3504	(conduct\$7 near1 (layer or region or medium)) and substrate	USPAT;	2004/04/21 16:48
		and clad\$6	EPO; JPO;	
10	40	(1)07 1 (1) 1 1	DERWENT	0004 (04 (04 4 4 4 4 4 4 4 4 4 4 4 4 4 4
18	42	(conduct\$7 near1 (layer or region or medium)) and substrate	USPAT;	2004/04/21 16:48
		and clad\$6 and (In near5 Ga near5 N)	EPO; JPO;	
10	1.4	//1	DERWENT	2004/04/04 46 52
19	14	((conduct\$7 near1 (layer or region or medium)) same (In	USPAT;	2004/04/21 16:52
		near5 Ga near5 N))	EPO; JPO; DERWENT	
20	88	 In"x"Ga"1-x"N		2004 (04 (21 16 55
20	00	III X Ga 1-X IV	USPAT; US-PGPUB;	2004/04/21 16:55
			EPO; JPO;	
			DERWENT	
21	3	In"x"Ga"1-x"N and (conduct\$7 near1 (layer or region or	USPAT:	2004/04/21 16:55
	3	medium)) and substrate and clad\$6	US-PGPUB;	2004/04/21 10.55
		meaning and substitute and claupo	EPO; JPO;	
			DERWENT	